



<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)				ATTY. DOCKET NO. 004393 USA C/01/MTCG/PCTRL		SERIAL NO. 10/686,589	
				APPLICANT Sasson R. SOMEKH et al.			
				FILING DATE October 17, 2003		GROUP 2125	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>11/1</i>	6,381,564 B1	04/30/02	David et al.			05/03/99	
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EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>5/1/05</i>			

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		<b>APPLICANT</b> Sasson R. SOMEKH et al.	
		<b>FILING DATE</b> October 17, 2003	<b>GROUP</b> 2125
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>			
<i>Mu</i>	September 15, 2004. Office Action for U.S. Serial No. 10/632,107, filed August 1, 2003.		
<i>J</i>	September 29, 2004. Office Action for U.S. Serial No. 09/363,966, filed July 29, 1999.		
<i>J</i>	October 1, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US03/23964.		
<i>J</i>	October 6, 2004. Office Action for U.S. Serial No. 10/759,108, filed January 20, 2004.		
<i>J</i>	October 12, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/19061.		
<i>Mu</i>	November 17, 2004. Written Opinion for PCT Serial No. PCT/US01/27407.		
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**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>Mu</i>	EP 0 932 195 A1	07/28/99	EP			X	
	EP 1 083 470 A2	03/14/01	EP			X	
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